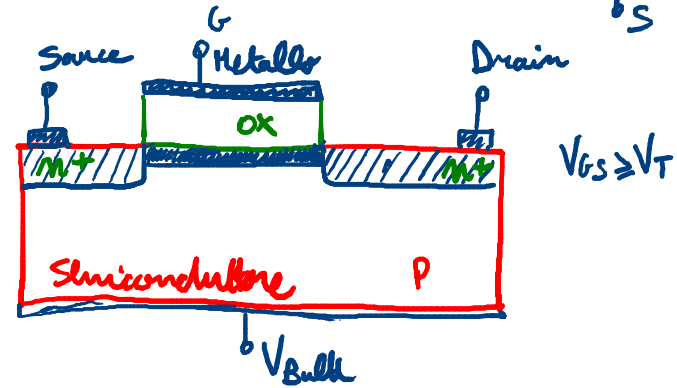


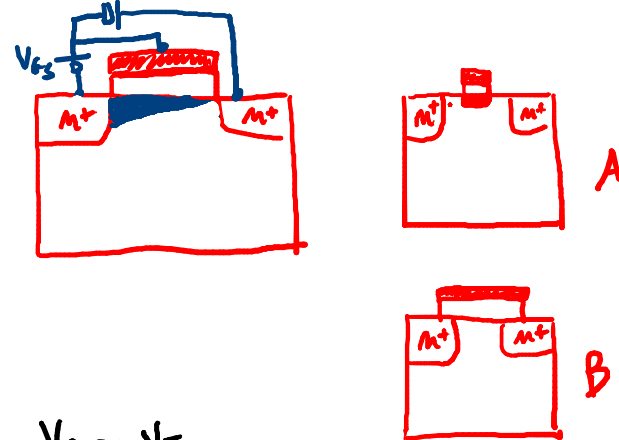
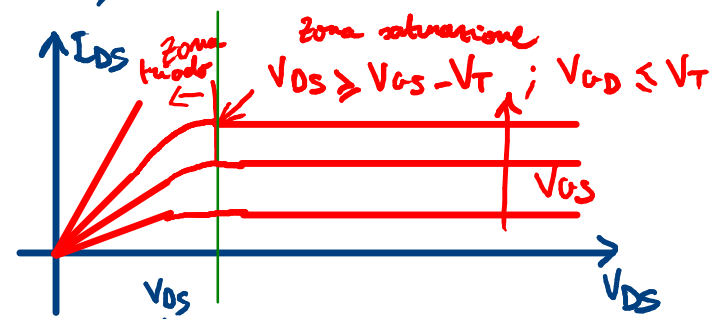
# FET Field Effect Transistor

MOSFET  
 Metal Oxide Semiconductor



$V_{GS} < V_T$   $I_{DS} = 0 A$  : Inibizione

$V_{GS} > V_T$  Inversione

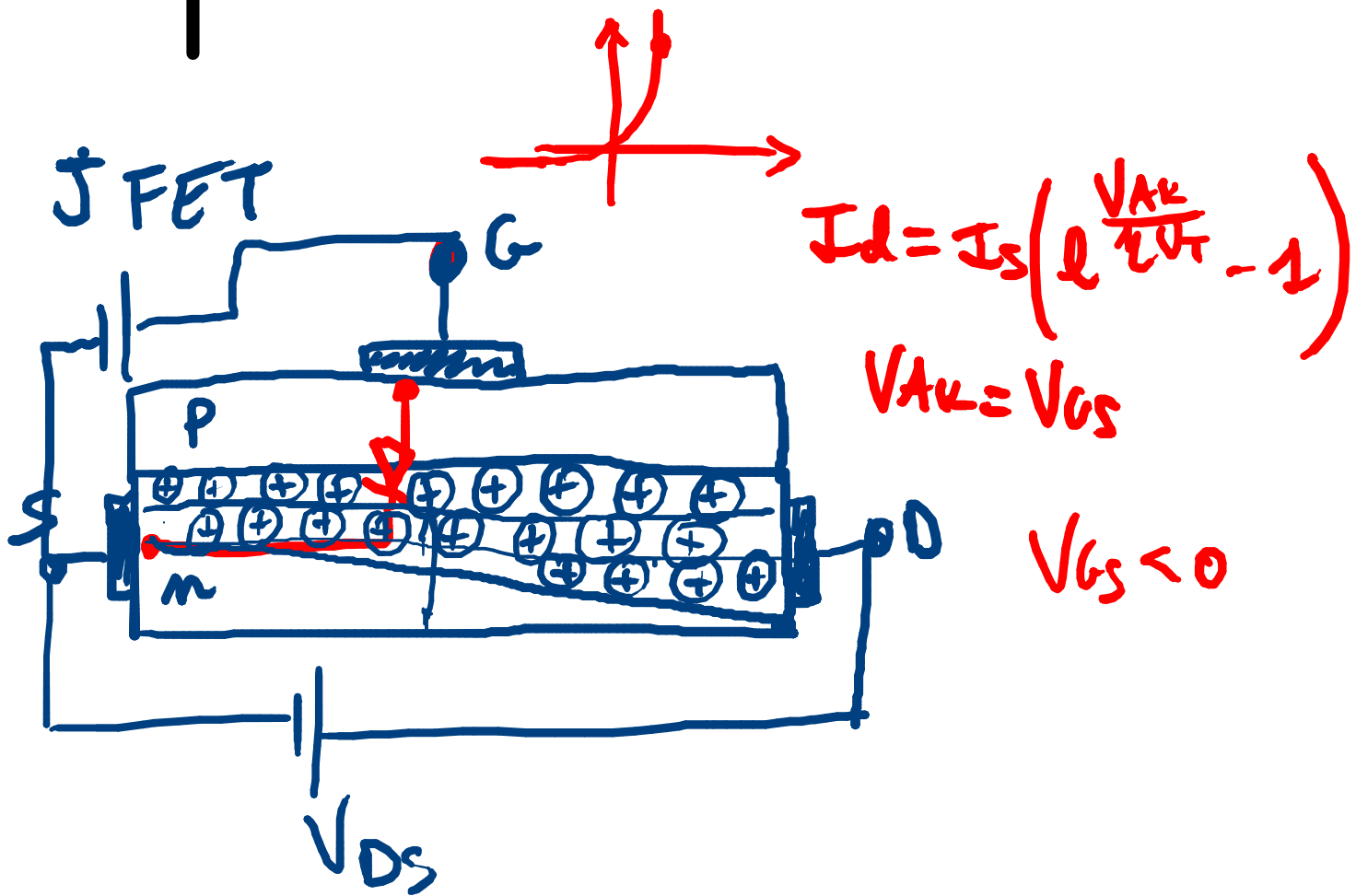
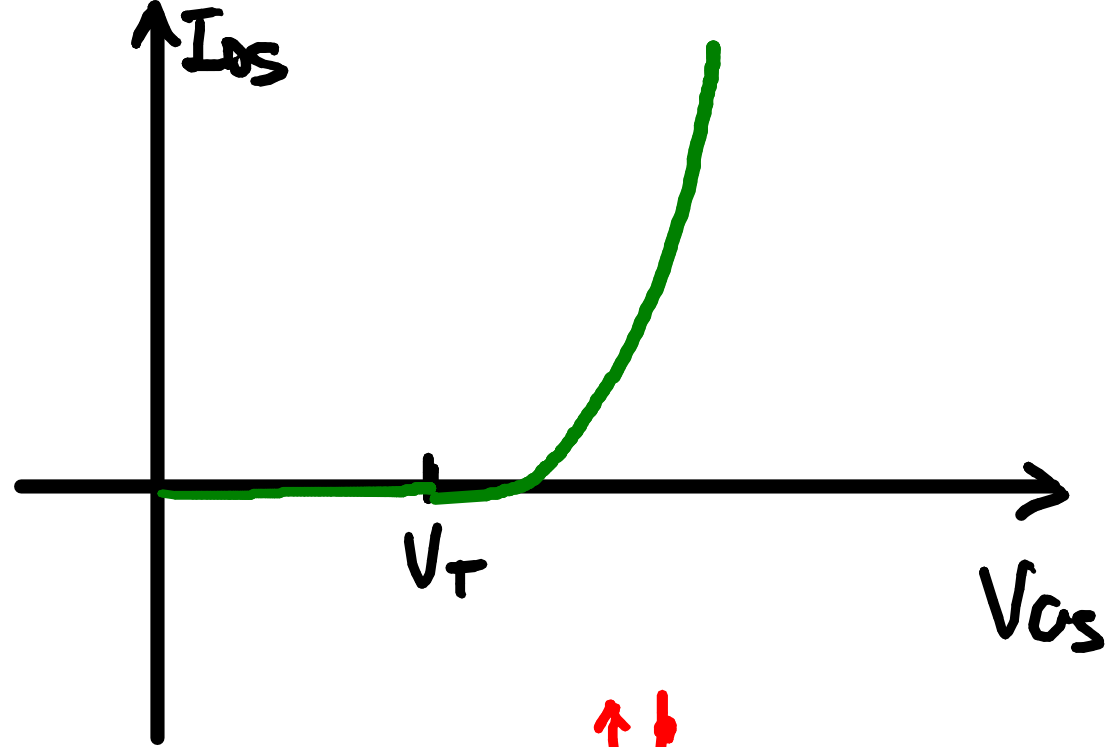


$V_{GS} > V_T$

$$\begin{aligned}
 V_{DS} < V_{GS} - V_T \quad I_{DS} &= \mu_n \frac{C_{ox} W}{2L} V_{DS} (V_{GS} + V_{GS} - V_{DS} - 2V_T) = \\
 &= \frac{\mu_n C_{ox} W}{2L} V_{DS} (V_{GS} + V_{GS} - V_{DS} - 2V_T) = \\
 &= \frac{\mu_n C_{ox} W}{2L} V_{DS} (V_{GS} + V_{GS} - V_{DS} + V_{GS} - V_{GS} - 2V_T) \\
 &= \frac{\mu_n C_{ox} W}{2L} V_{DS} (2V_{GS} - V_{DS} - 2V_T) \\
 &= \frac{\mu_n C_{ox} W}{2L} [2V_{GS}V_{DS} - V_{DS}^2 - 2V_{DS}V_T] = \\
 &= \frac{\mu_n C_{ox} W}{2L} [2(V_{GS} - V_T)V_{DS} - V_{DS}^2] = \\
 &= \frac{\mu_n C_{ox} W}{L} [(V_{GS} - V_T)V_{DS} - \frac{V_{DS}^2}{2}]
 \end{aligned}$$

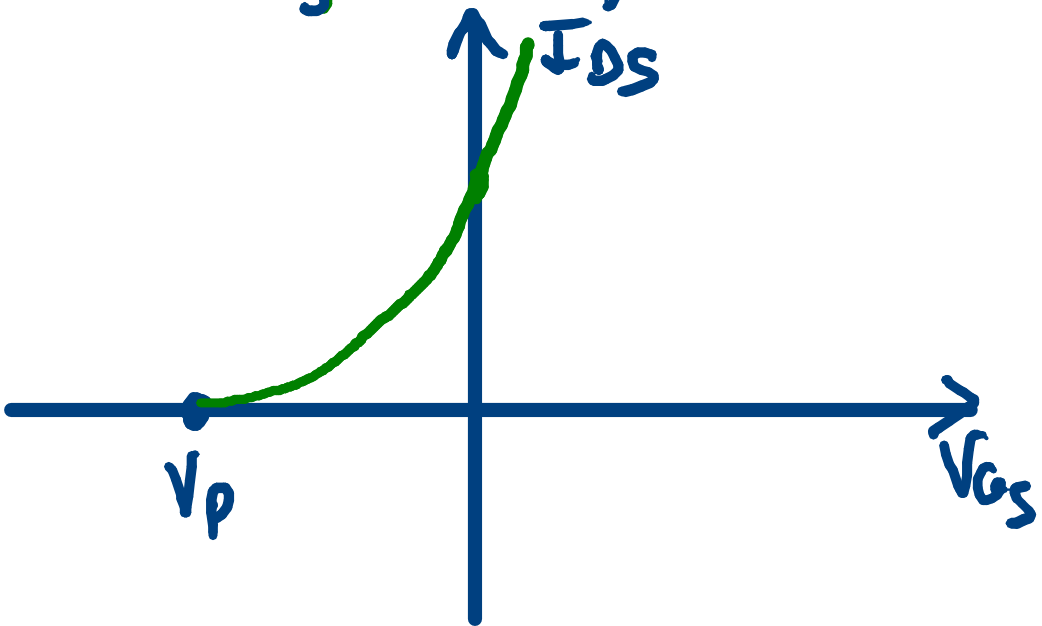
$$V_{DS} = V_{GS} - V_T$$

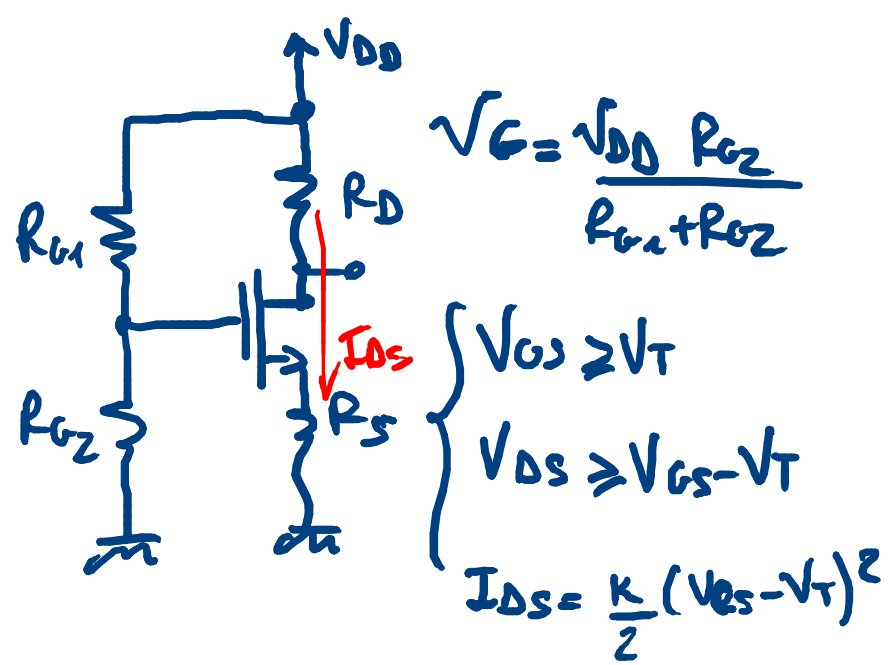
$$I_{DS} = \frac{\mu_n C_{ox} W}{2L} (V_{GS} - V_T)^2$$



$$I_{DS} = k_j V_{GS} (V_{GS} + V_{G0} - 2V_p)$$

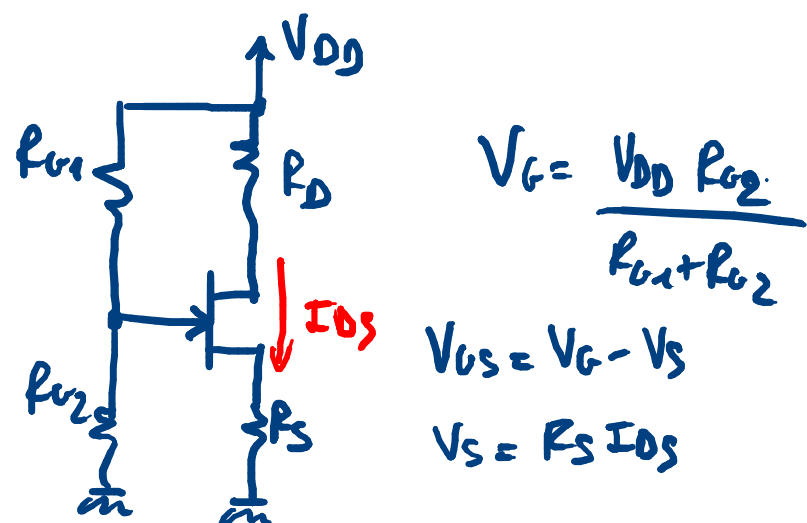
$$I_{DS} = k_j (V_{GS} - V_p)^2$$



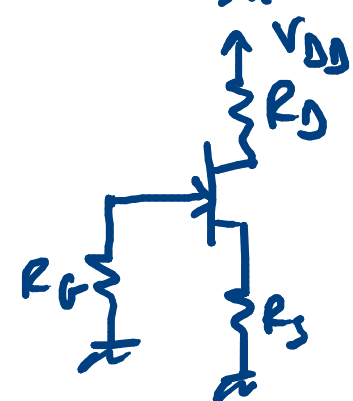


$I_D = I_S$  *multi*  $I_D = 0A$   $K = \mu_n C_{ox} \cdot W/L$

$$\begin{cases} V_{DD} = (R_S + R_D)I_{DS} + V_{DS} \\ I_{DS} = \frac{K}{2}(V_{GS} - V_T)^2 \\ V_G = \frac{R_{G2}}{R_{G1} + R_{G2}} V_{DD} \end{cases}$$

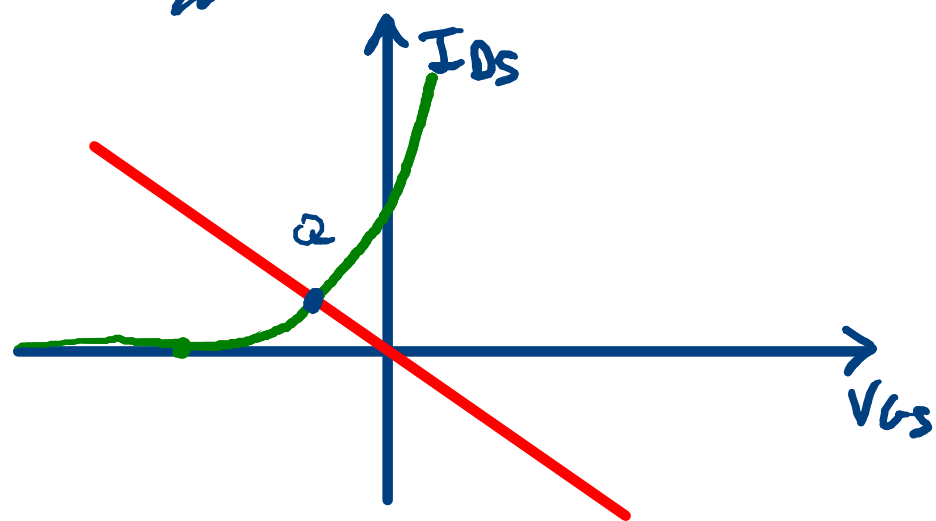


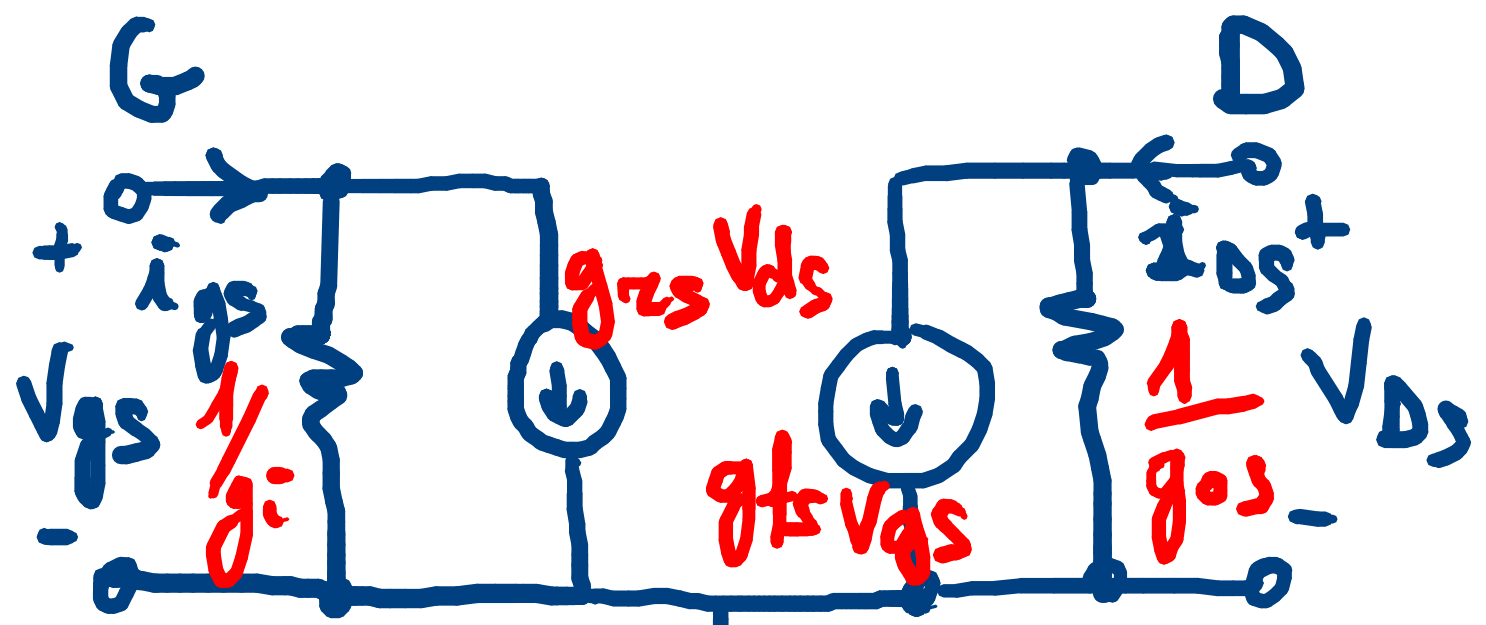
$$V_{GS} = V_G - R_S I_{DS}$$



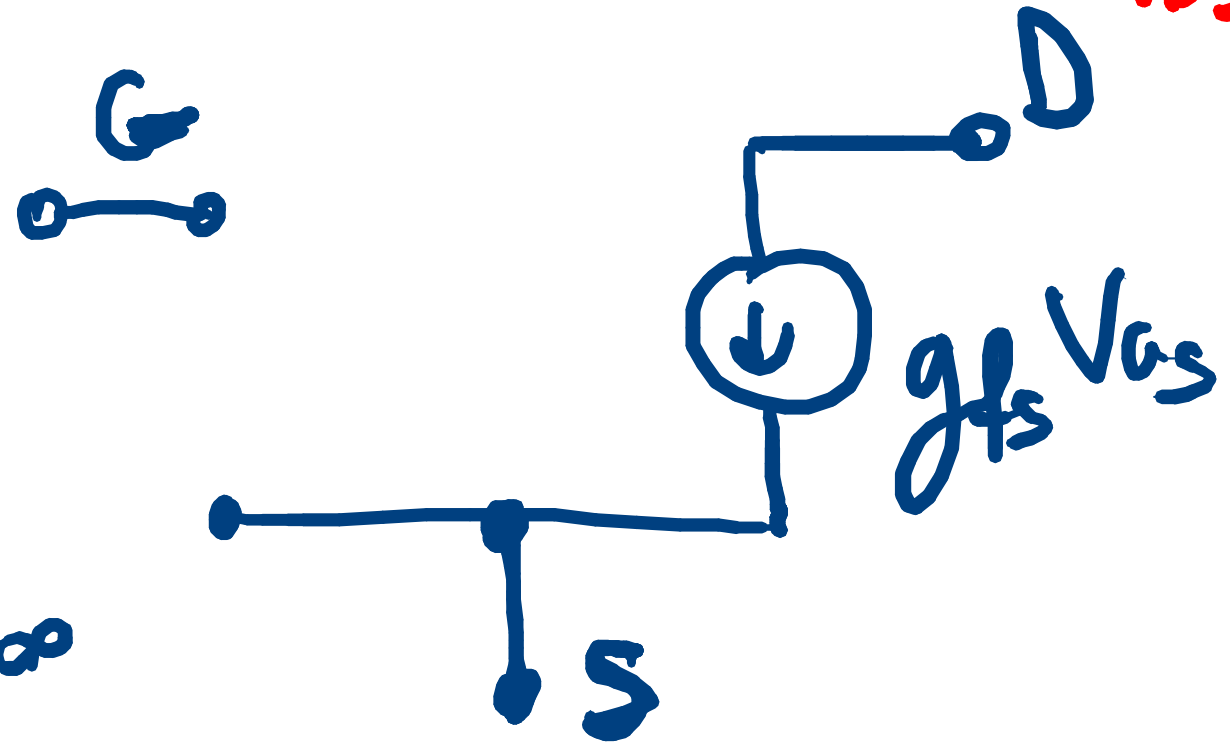
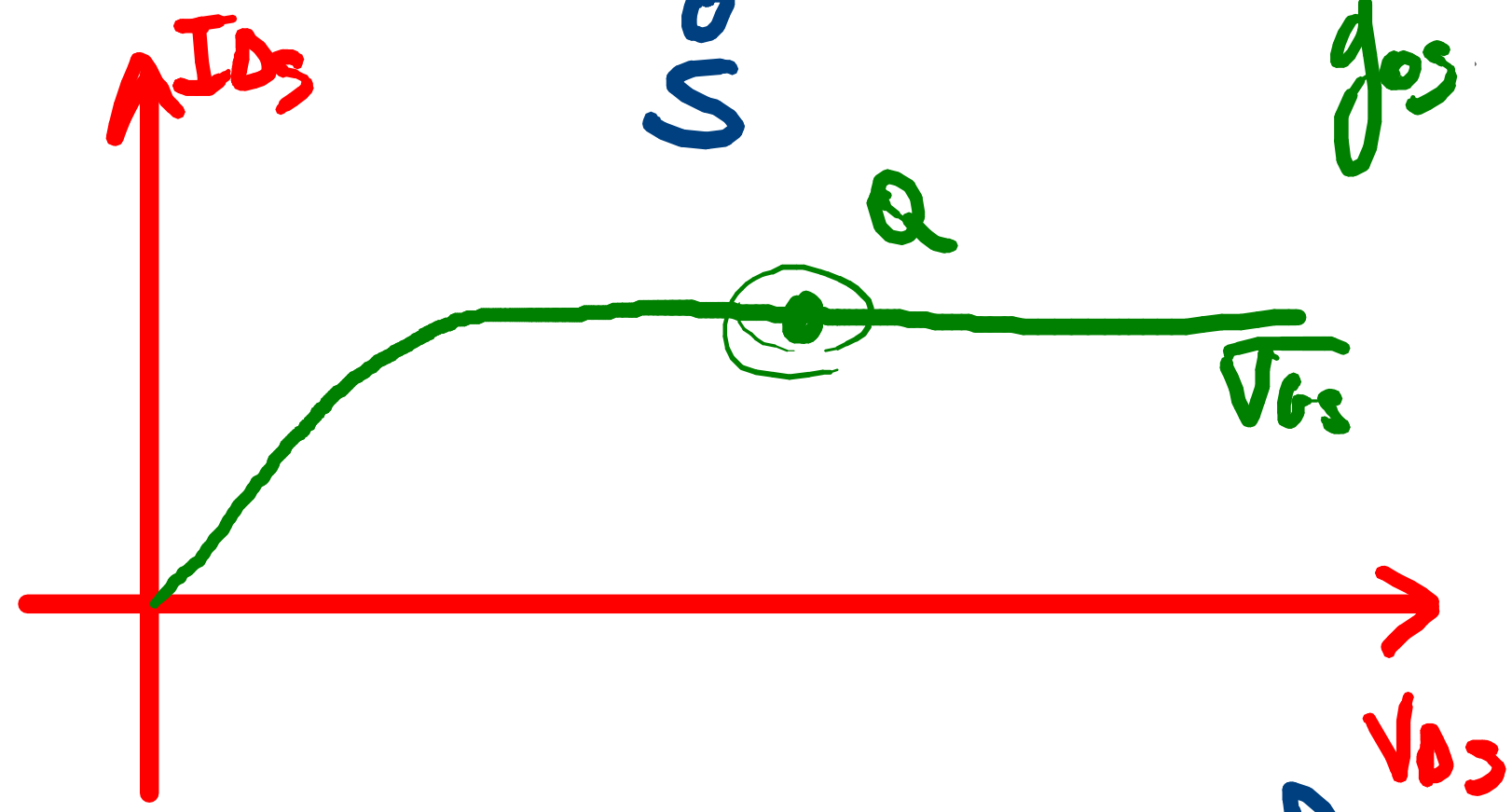
$$V_G = 0V$$

$$\underline{V_{GS} = V_G - V_S = -R_S I_{DS}}$$

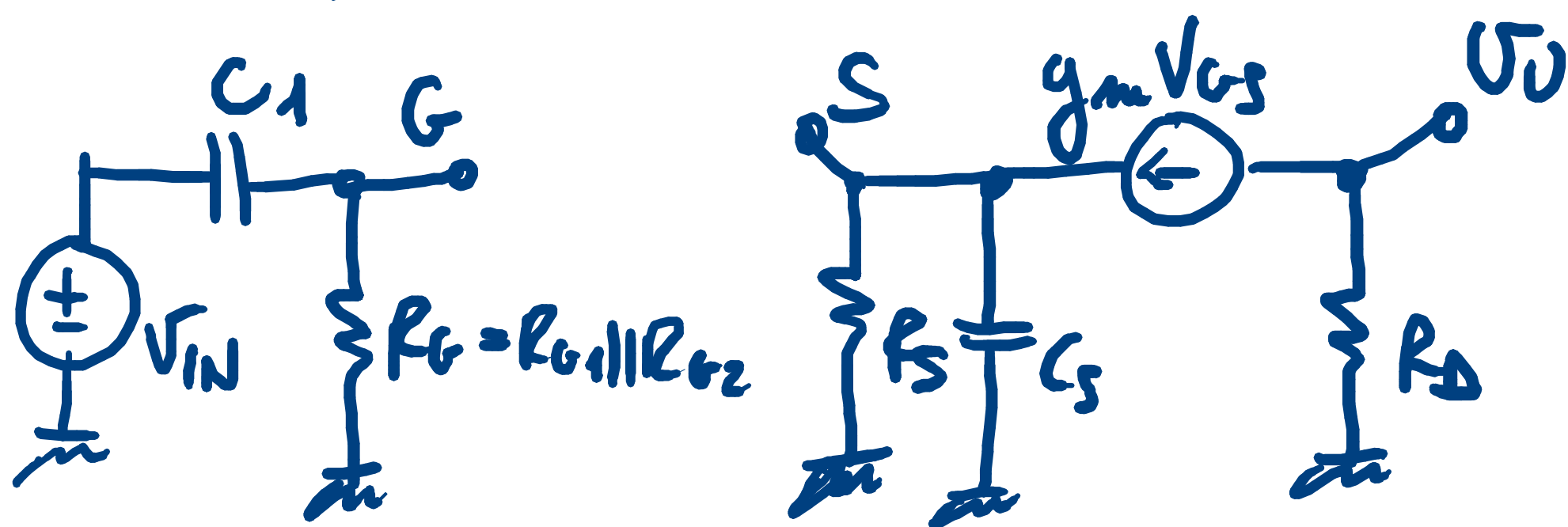
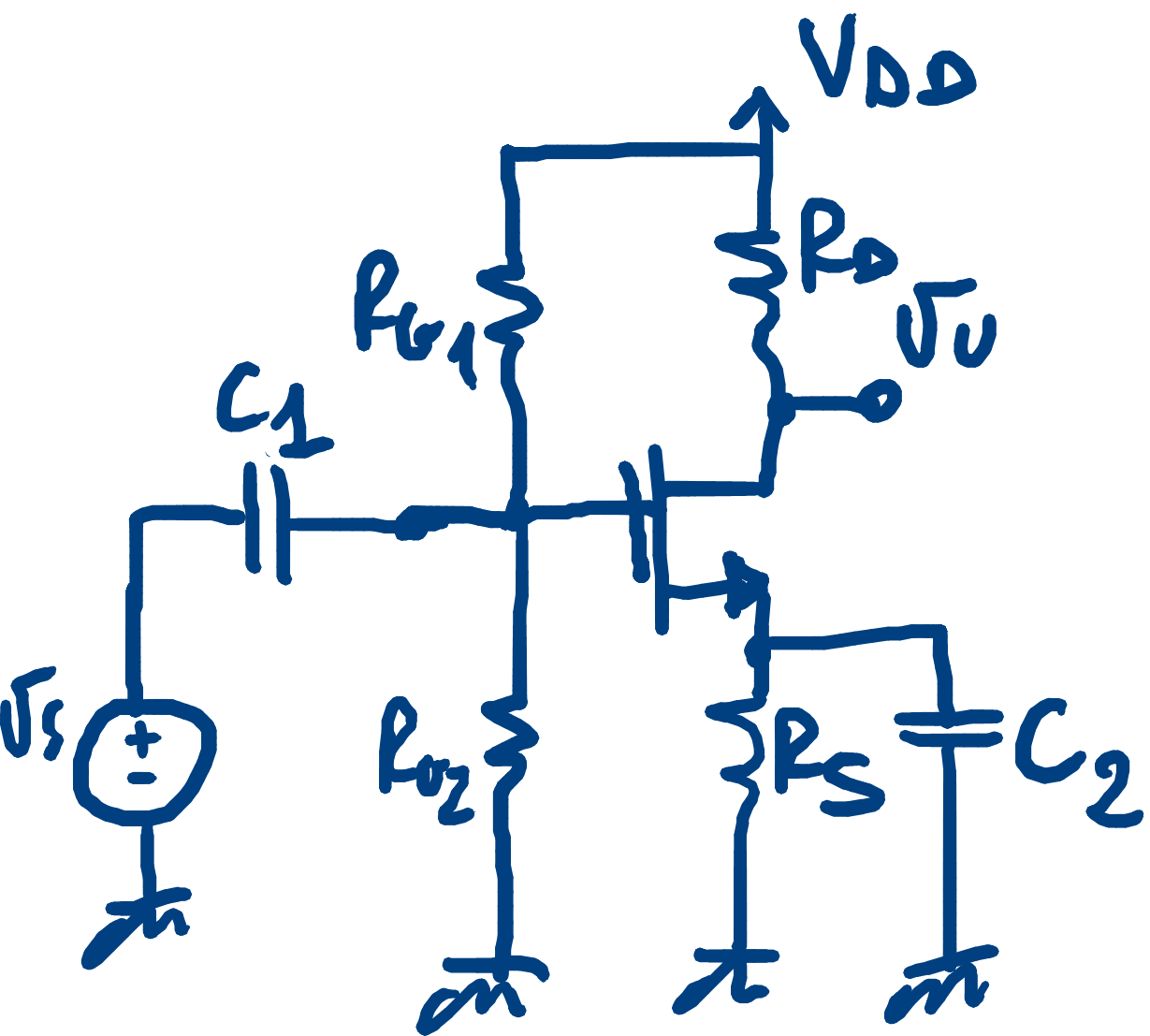




$$g_{os} = \left. \frac{\partial I_{DS}}{\partial V_{DS}} \right|_{V_{GS}}$$



$h_{ie} \rightarrow r_{\pi}$   
 $\frac{h_{fe}}{h_{ie}} \rightarrow g_m$



$$A_V(s) = \frac{V_U(s)}{V_{IN}(s)} = k \frac{N(s)}{D(s)} = k \frac{\prod_{i=1}^M (s - S_{oi})}{\prod_{j=1}^N (s - S_{pi})}$$